
2SK322

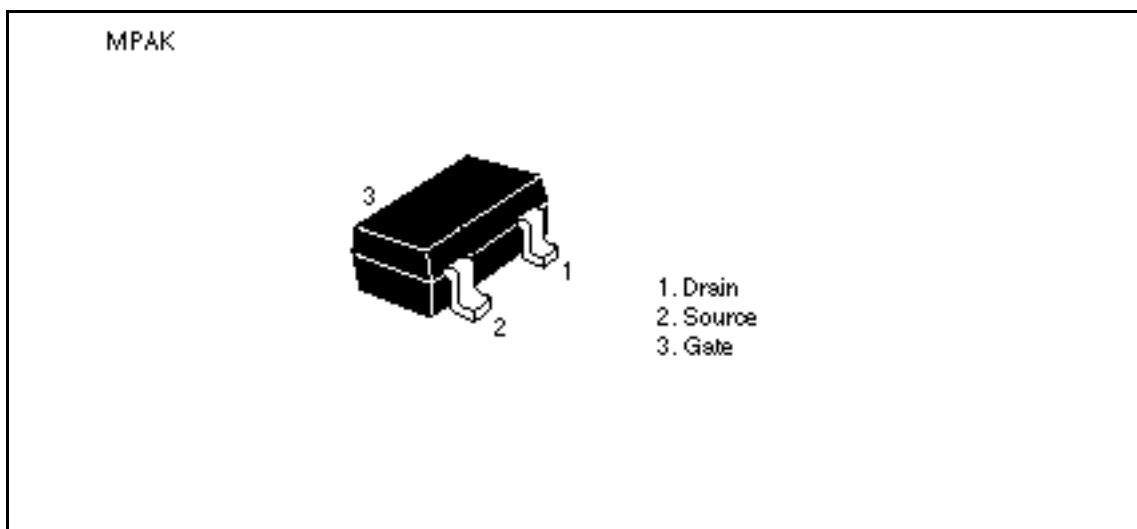
Silicon N-Channel Junction FET

HITACHI

Application

HF wide band amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Gate to drain voltage	V_{GDO}	-15	V
Gate to source voltage	V_{GSO}	-15	V
Drain current	I_D	50	mA
Gate current	I_G	5	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

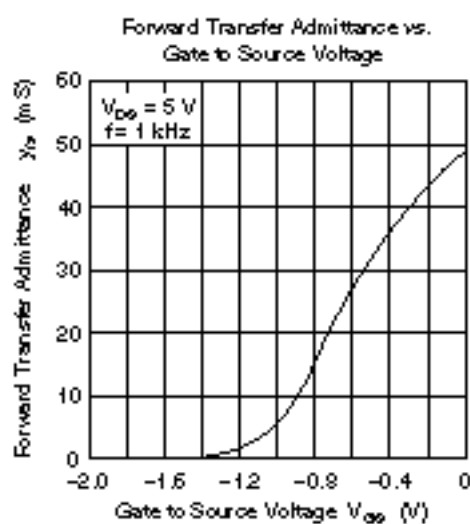
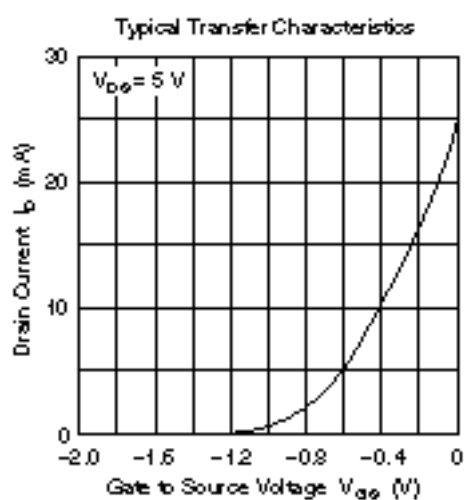
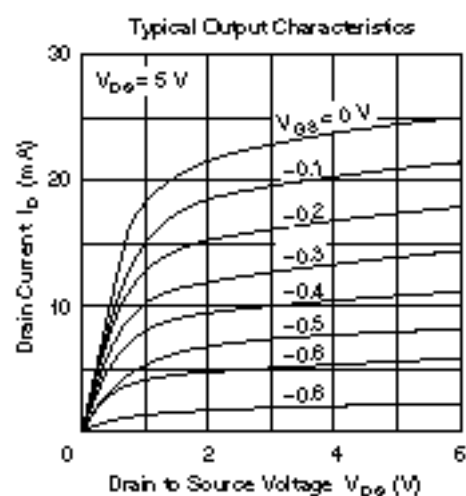
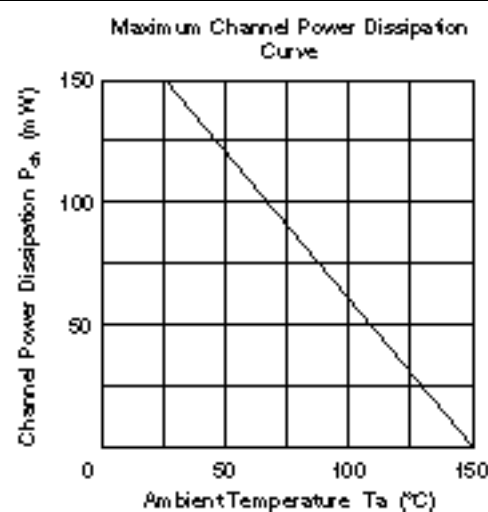
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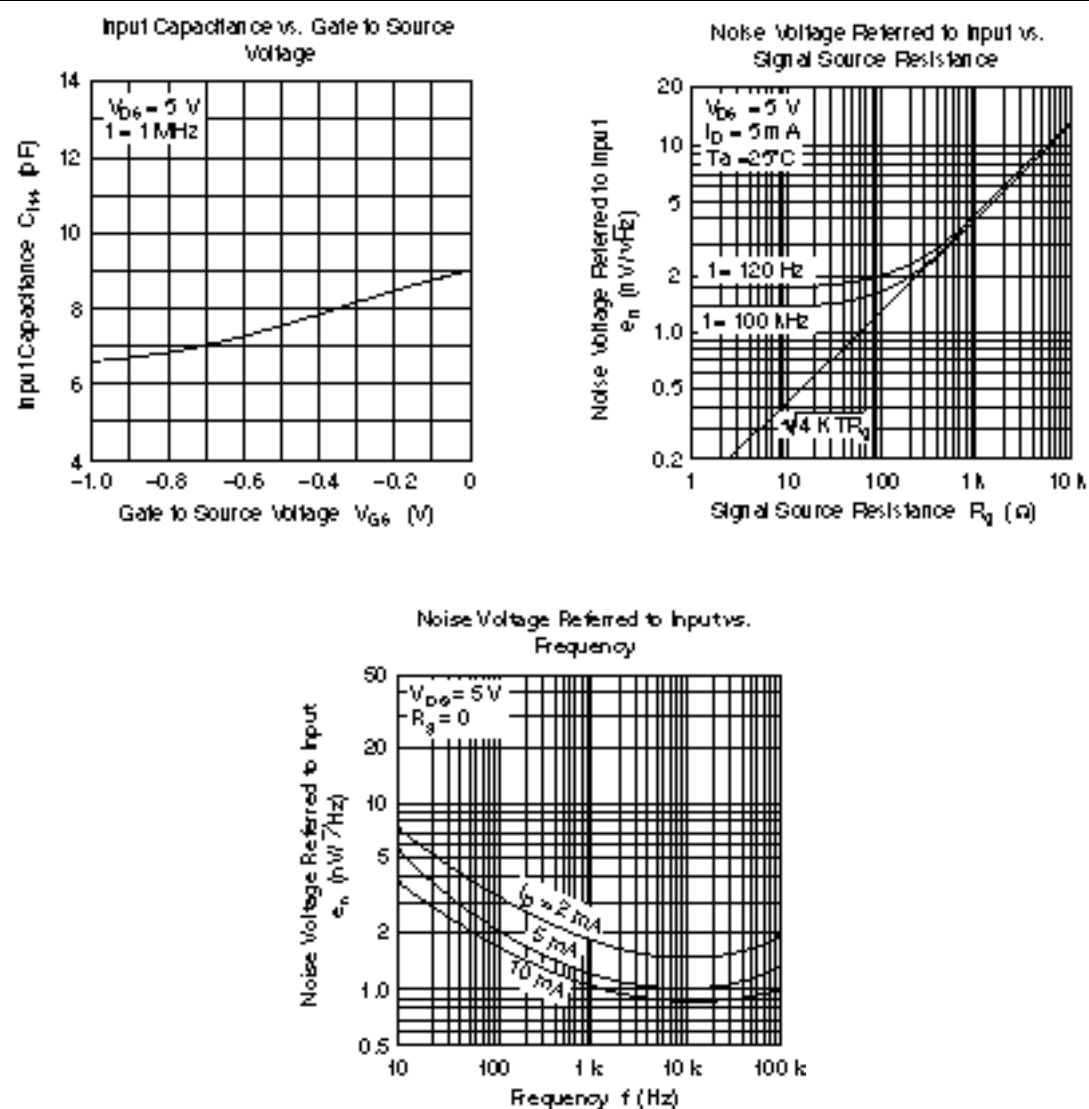
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to drain breakdown voltage	$V_{(BR)GDO}$	-15	—	—	V	$I_G = -100 \mu A$
Gate to source breakdown voltage	$V_{(BR)GSO}$	-15	—	—	V	$I_G = -100 \mu A$
Gate cutoff current	I_{GSS}	—	—	-10	nA	$V_{GS} = -7 V, V_{DS} = 0$
Drain current	I_{DSS}^{*1}	5	—	50	mA	$V_{DS} = 5 V, V_{GS} = 0$ (pulse)
Gate to source cutoff voltage	$V_{GS(off)}$	—	—	-3.0	V	$V_{DS} = 5 V, I_D = 100 \mu A$
Forward transfer admittance	$ y_{fs} $	25	45	—	mS	$V_{DS} = 5 V, V_{GS} = 0, f = 1 \text{ kHz}$

Note: 1. The 2SK322 is grouped by I_{DSS} as follows.

Grade	P	Q	R	S	T
Mark	WP	WQ	WR	WS	WT
I_{DSS}	5 to 16	14 to 24	20 to 32	28 to 42	36 to 50





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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel Tokyo (03) 3270-2111

Fax (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Berkeley, CA 94705-1835

U.S.A.

Tel 415-589-8300

Fax 415-583-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Dannebrogstrasse 3

D-85622 Feldkirchen

München

Tel 089-9 91 80-0

Fax 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

High Wycombe

Berkshire SL6 6SYA

United Kingdom

Tel 0628-885000

Fax 0628-778322

Hitachi Asia Pte. Ltd.

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0404

Tel 535-2100

Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel 27359218

Fax 27308074